

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-11 (Canceled).

Claim 12 (Original): A semiconductor device comprising:

a substrate;

a transistor having a pair of source/drain regions formed in said substrate, a gate electrode formed via a gate dielectric film on a channel region sandwiched between said pair of source/drain regions, and a side wall formed on a side surface of said gate electrode;

an interlayer dielectric film formed on said transistor;

source/drain wirings formed on said interlayer dielectric film; and

conductors formed in said interlayer dielectric film for connecting said source/drain wirings to said source/drain regions, wherein said side wall is constructed with a porous material.

Claim 13 (Original): A semiconductor device comprising:

a substrate;

a transistor having a pair of source/drain regions formed in said substrate and a gate electrode formed via a gate dielectric film on a channel region sandwiched between said pair of source/drain regions;

an interlayer dielectric film formed on said transistor;

source/drain wirings formed on said interlayer dielectric film; and

conductors formed in said interlayer dielectric film for connecting said source/drain wirings to said source/drain regions, wherein

said interlayer dielectric film is formed except for a region between said gate electrode and said conductors.